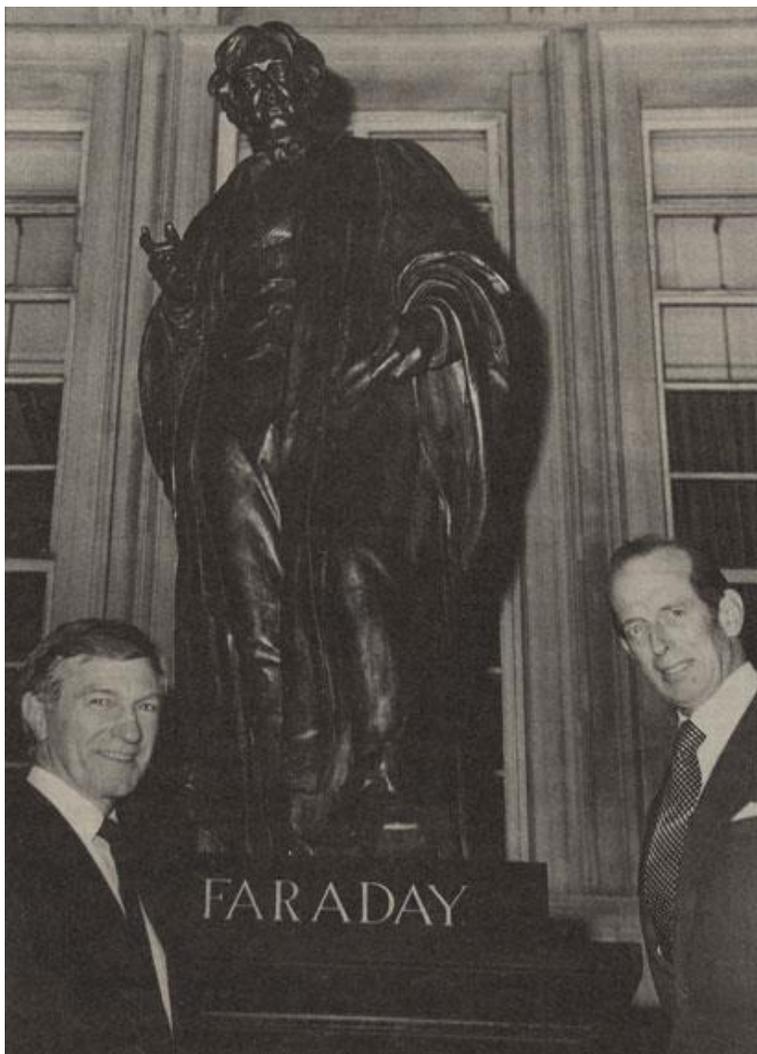


深耕底层数据，实现精准揭示

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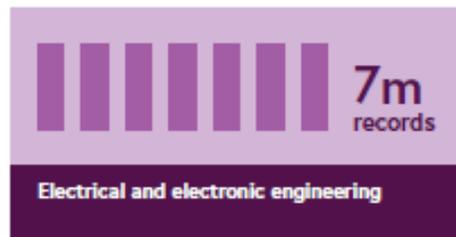
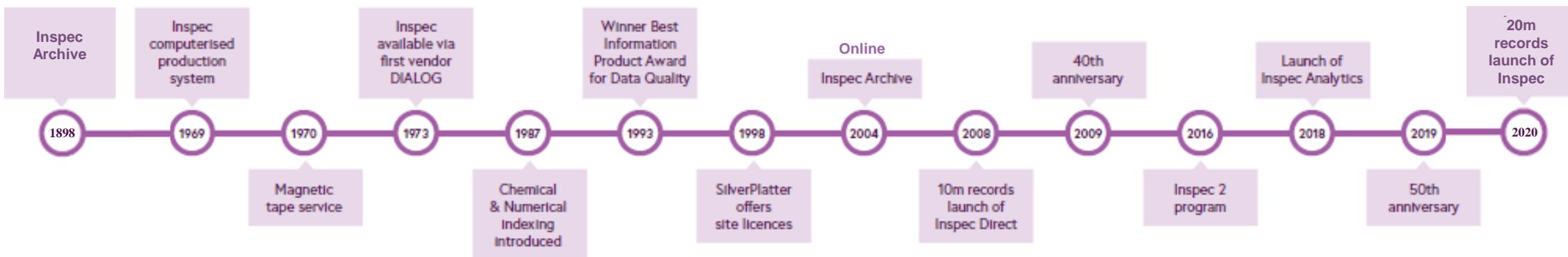
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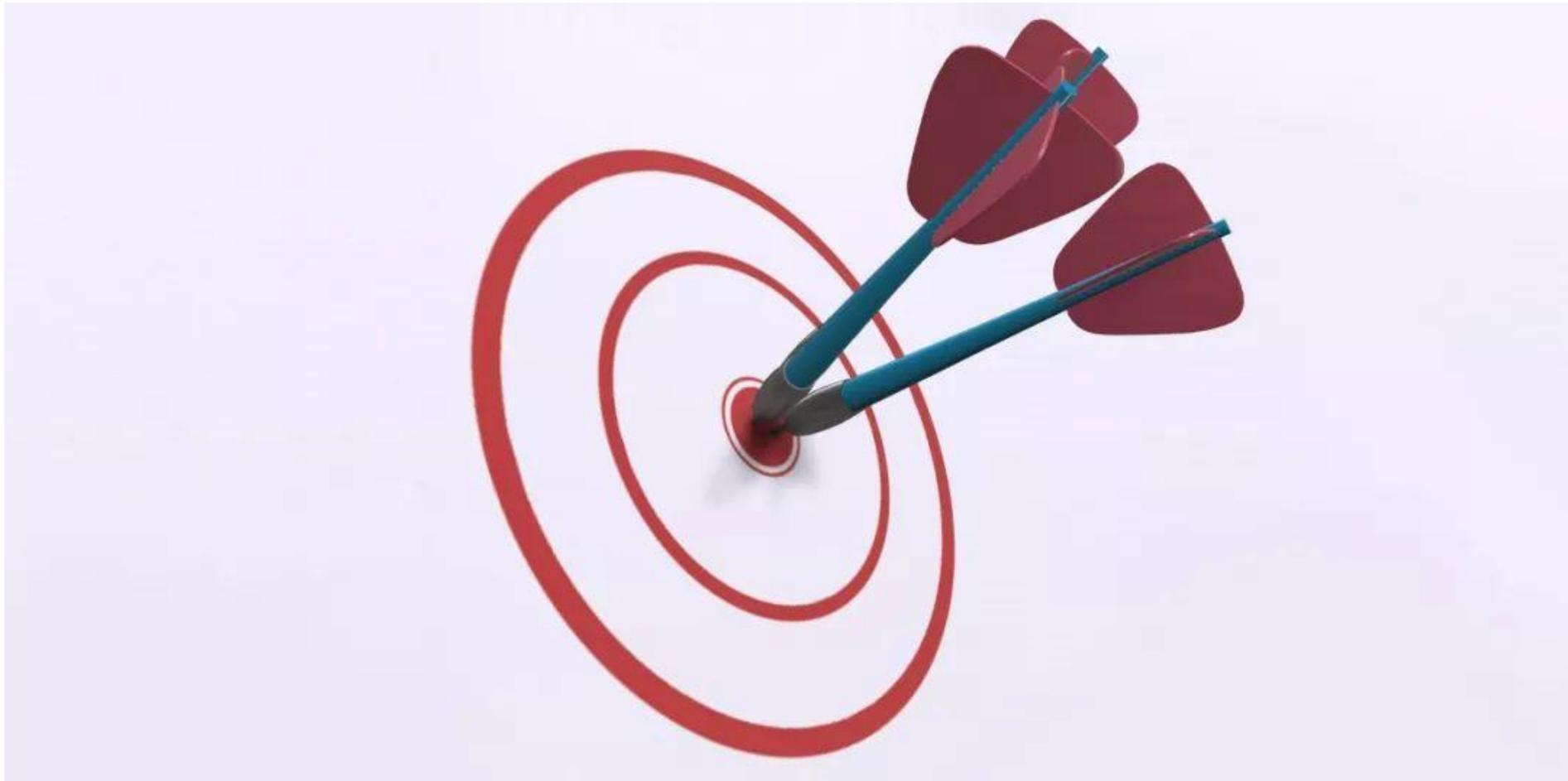
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HST/WFPC2 snapshot imaging of symbiotic stars

作者: [Brocksopp, C.](#); [Bode, M.F.](#); [Eyres, S.P.S.](#)

DOI: 10.1046/j.1365-8711.2003.06915.x

HST/WFPC2 snapshot imaging of symbiotic stars

作者: Brocksopp, C.; Bode, M.F.; Eyres, S.P.S.

查看 [Web of Science ResearcherID](#) 和 [ORCID](#) (由 Clarivate Analytics 提供)

Monthly Notices of the Royal Astronomical Society

卷: 344 期: 4 页: 1264-70

DOI: 10.1046/j.1365-8711.2003.06915.x

出版年: 1 Oct. 2003

文献类型: Journal Paper

出版社原始摘要信息

摘要

The results of a HST/WFPC2 snapshot imaging survey of selected symbiotic stars in 1999/2000 are presented. Seven sources - HD 149427 (PC 11), PU Vul, RT Ser, He2-104 (Southern Crab), V1329 Cyg (HBV 475), V417 Cen and AS 201 - were observed in filters F218W (ultraviolet continuum), F502N ([O III] λ 4959, 5007) and F656N (H α 6563); an eighth source, RS Oph, was observed in F437N ([O III] λ 4363), F502N and F656N. The presence of extended emission was detected in He2-104, V1329 Cyg and possibly HD 149427. In He2-104, we detected the [O III] and H α counterparts to the inner lobes found in [N II] by Corradi et al. For V1329 Cyg, comparison with previously published HST/FOC results indicates expanding ejecta which may be associated with an ejection event in 1982 (+or-2 yr) at a velocity of 260 +or- 50 km s⁻¹ in the plane of the sky and at an assumed distance of 3.4 kpc. We also present previously unpublished radio images of HD 149427, which we have obtained from the archives of the Australia Telescope Compact Array and which reveal the presence of extended emission at a similar orientation to that of the possible optical extension. Finally, we also include HST/WFPC2 GO observations of AG Peg and detect possible extended emission in the F218W filter.

作者信息

作者地址: Brocksopp, C.; Bode, M.F.; Astrophys. Res. Inst., Liverpool John Moores Univ., Birkenhead, UK.

出版商

Blackwell Science for R. Astron. Soc., UK

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类别 / 分类
研究方向: Astronomy & Astrophysics; Instruments & Instrumentation (由 Clarivate Analytics 提供)

天文学对象索引: He2-104; V417 Cen; AS 201; AG Peg; HD 149427; PU Vul; RT Ser; V1329 Cyg; RS Oph

IPC国际专利号索引: H05H1/02 Arrangements for confining plasma by electric or magnetic fields; Arrangements for heating plasma

化学物质索引: N/el; O/el

化学索引

分类代码: A9780G Cataclysmic binaries; A9710F Circumstellar shells and expanding envelopes; A9710H Mass transfer; A9580J Photographic region astronomical observations; A9580M Space ultraviolet astronomical observations; A9580D Radio, radar, and microwave astronomical observations

CODEN: MNRAA4

受控索引: binary stars; circumstellar matter; stellar photometry; stellar winds; stellarators; symbiotic stars

非受控索引: HST-WFPC2 snapshot imaging; symbiotic stars; ultraviolet continuum; Australia Telescope Compact Array; Hubble Space Telescope; Multielement Radio Linked Interferometer Network; nonthermal radio emission; F218W filter; outflows; winds; 3.4 kpc; N; O

文献信息
语言: English
入藏号: INSPEC:7934457
ISSN: 0035-8711
参考文献数: 20

其他信息
处理类型: Experimental

数值数据索引: galactic distance 3.4E+03 pc

SICI: 0035-8711(20031001)344:4L.1264:WSIS;1-S

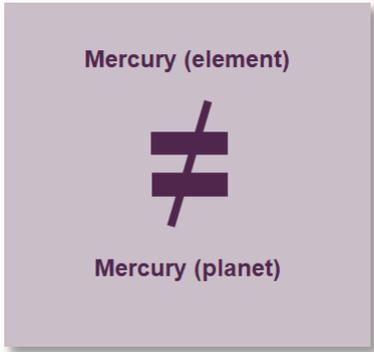
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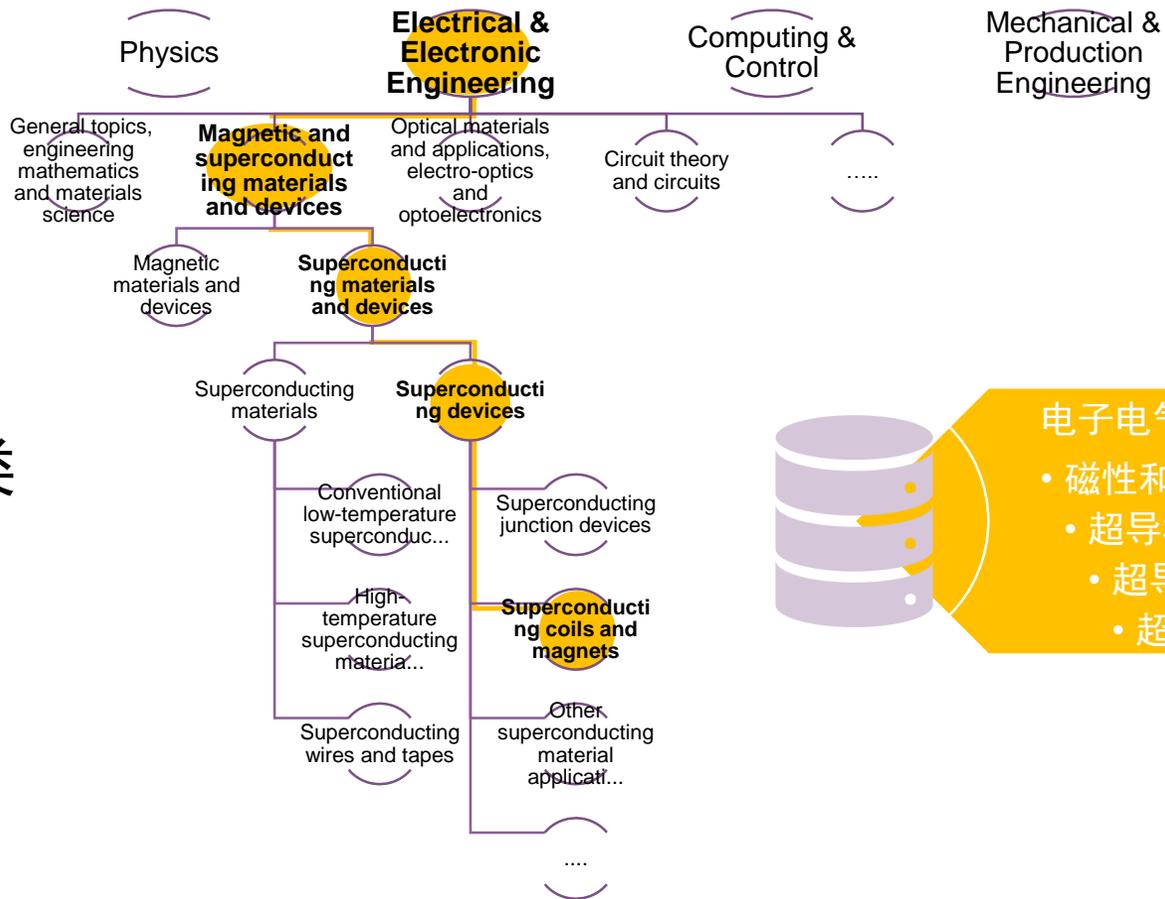
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9988 个控制词和10000+非控制词

叙词和学科分类

3571个学科分类



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- 超导装置
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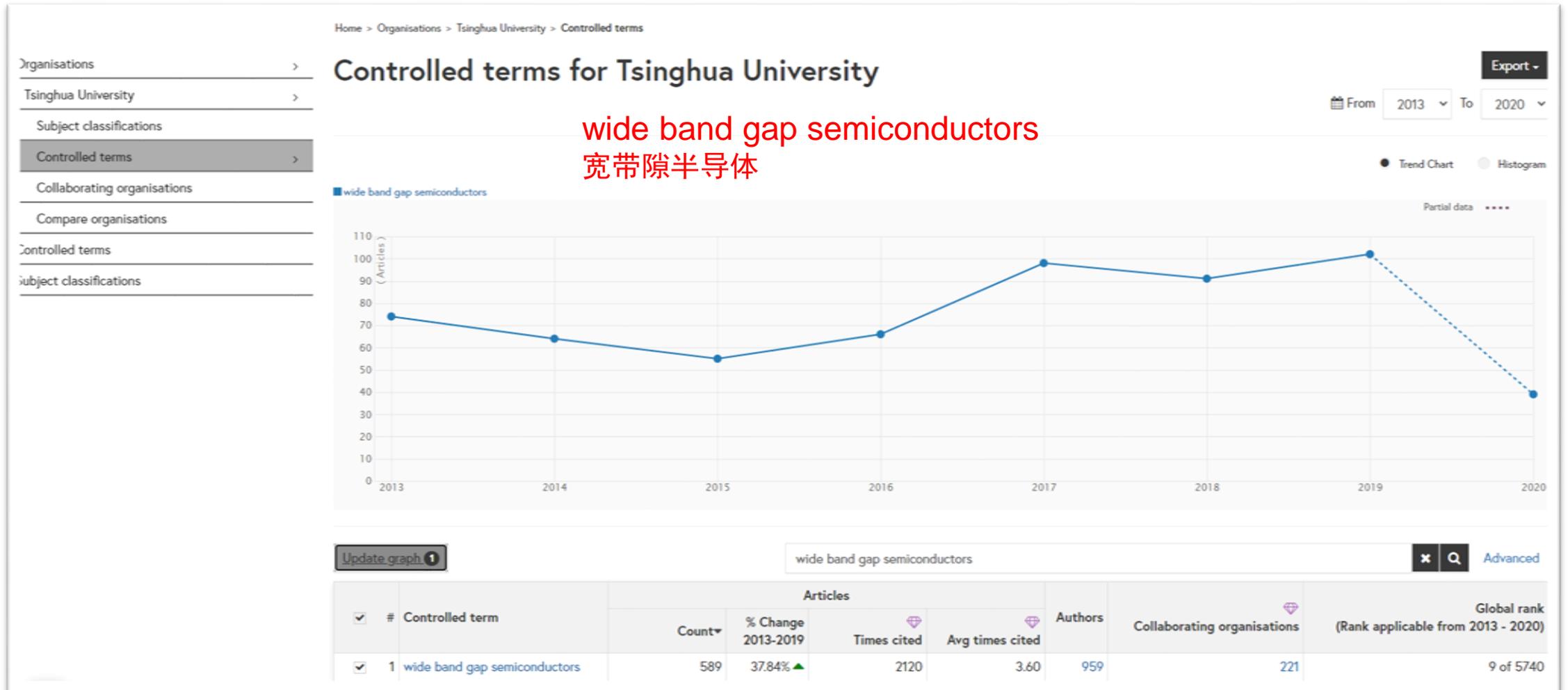
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 - 16K 学术机构, 5K 企业, 3K 政府机构
 - 1.2K 医疗单位, 3.3K 其他

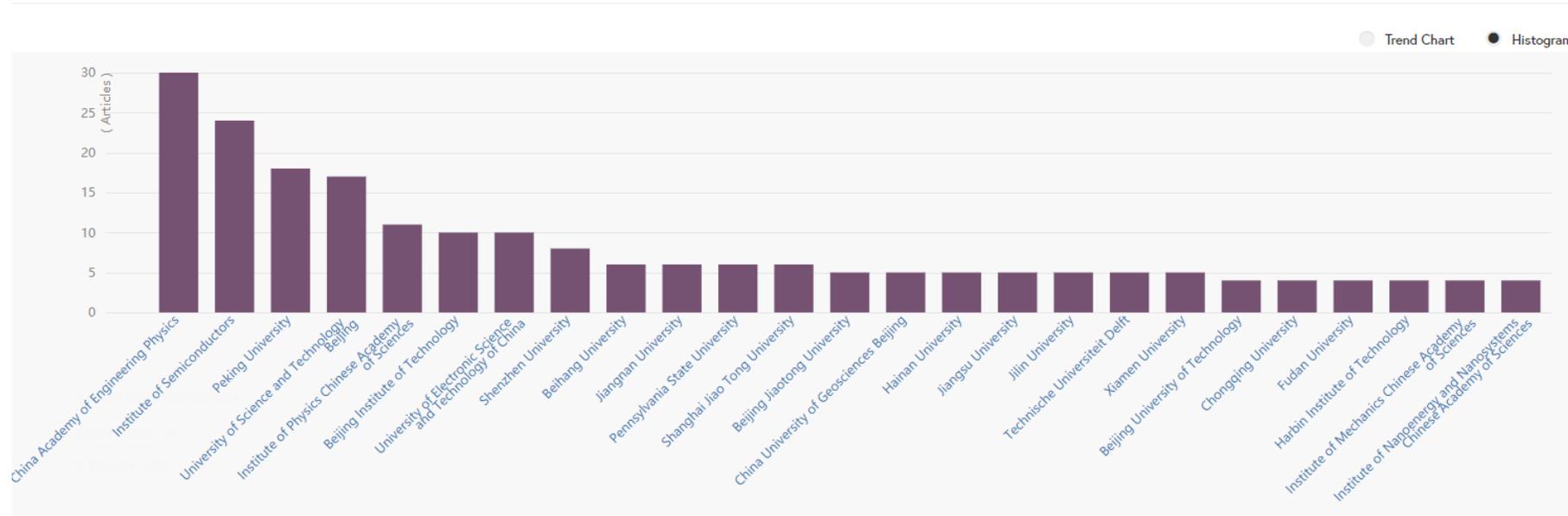


- Organisations >
- Tsinghua University >
- Subject classifications >
- Controlled terms >
- wide band gap semiconductors >
- Authors
- Collaborating organisations >**
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Organisations collaborating with Tsinghua University on wide band gap semiconductors

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From 2013 To 2020



Update graph 25

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<input checked="" type="checkbox"/>	#	Collaborating organisations	Collaborations	% Change 2013-2019
<input checked="" type="checkbox"/>	1	China Academy of Engineering Physics Mianyang, China Academic	30	n/a
<input checked="" type="checkbox"/>	2	Institute of Semiconductors Beijing, China	24	-85.71%



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Controlled terms for Chang'an University [view online](#)

Report showing 1 to 25 of total 3550 Controlled terms

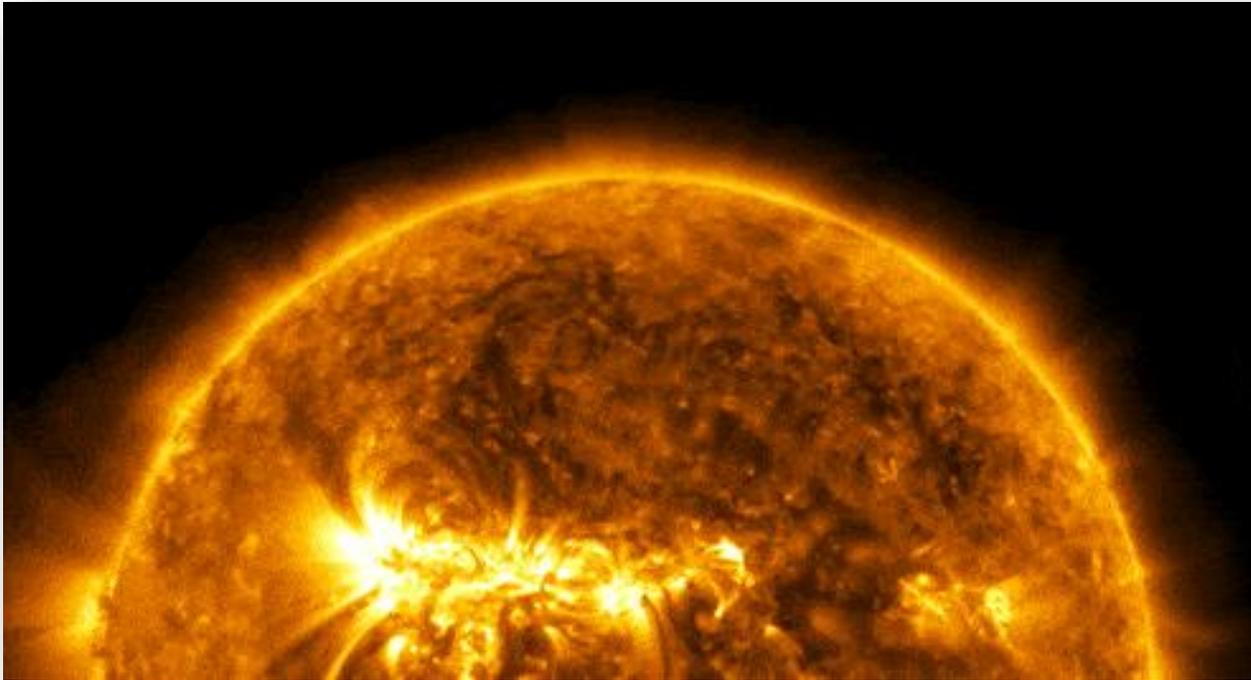
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roads	654	51.19%	529	0.81	1200	130	1 of 2988
wide band gap semiconductors	649	152.38%	950	1.46	903	112	1 of 5740

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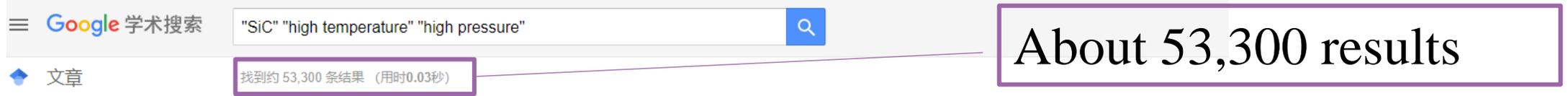


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关键字检索

Key words: SiC+high temperature+high pressure



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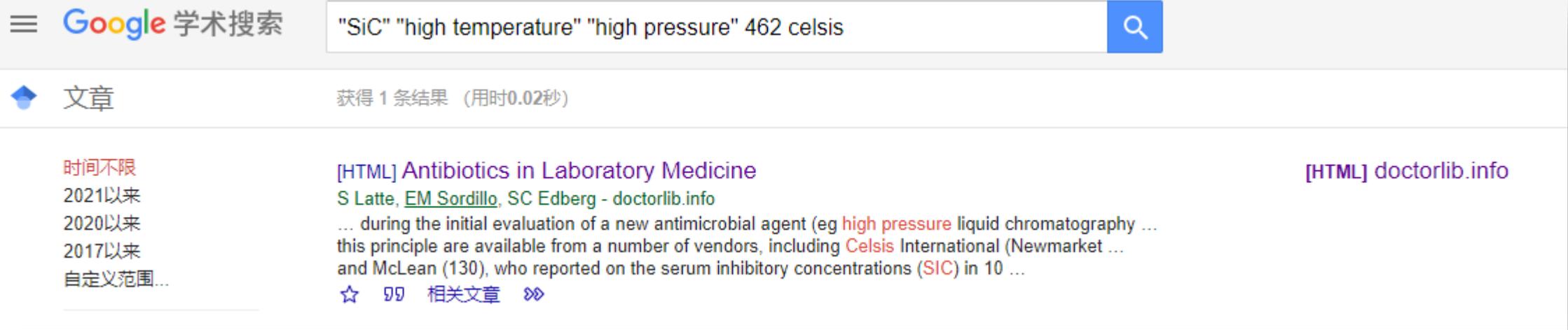
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About 53,300 results

时间不限
2021以来
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Oxidation of SiC powder by high-temperature, high-pressure H₂O
M Yoshimura, J Kase, S Sōmiya - Journal of Materials Research, 1986 - Springer
The reaction between SiC powder and H₂O has been studied at 400°–800° C under 10

[PDF] researchgate.net



Google 学术搜索 "SiC" "high temperature" "high pressure" 462 celsius

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2017以来
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[HTML] Antibiotics in Laboratory Medicine
S Latte, EM Sordillo, SC Edberg - doctorlib.info
... during the initial evaluation of a new antimicrobial agent (eg high pressure liquid chromatography ... this principle are available from a number of vendors, including Celsis International (Newmarket ... and McLean (130), who reported on the serum inhibitory concentrations (SiC) in 10 ...
☆ 99 相关文章 99

[HTML] doctorlib.info

Synthesis and sintering of SiC under high pressure and high temperature
SK Bhaumik, C Divakar, SU Devi, AK Singh - Journal of materials research, 1999 - Springer
Starting from elemental powders, simultaneous synthesis and compaction of SiC were conducted at 3 GPa pressure and temperatures in the range 2100–2900 K. The sintered compacts were characterized by x-ray diffraction, microhardness measurements, and ...
☆ 99 被引用次数: 25 相关文章 所有 11 个版本

[PDF] semanticscholar.org

Tribological characteristics of SiC ceramics in high-temperature and high-pressure water
S Kitaoka, T Tsuji, T Katoh... - Journal of the ..., 1994 - Wiley Online Library
The effects of temperature and sliding speed on the tribological behavior of a SiC ceramic by sliding on the same material in deoxygenated water were investigated from room temperature to 300° C under the corresponding saturated vapor pressures. The friction ...
☆ 99 被引用次数: 42 相关文章 所有 6 个版本

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semiconductor devices



主题



And



9.32E+06



至

示例: 1.9E+03



pressure (pascal)



And



7.35E+02



至

示例: 1.9E+03



temperature (kelvin)



And



SiC/bin



所有化学特征描述



检索

检索提示

+添加行 | 重设

时间跨度

所有年份 (1898 - 2021)

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检索结果: 28

(来自 Inspec)

您的检索: 主题: (semiconductor devices) AND 压力: $\geq(9.32E+06)$ AND 温度: $\geq(7.35E+02)$ AND 化学物质索引: (SiC/bin) ...更多内容

 创建跟踪

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在如下结果集内检索...



过滤结果依据:

  开放获取 (5)

精炼

出版年

- 2020 (3)
- 2019 (1)
- 2018 (1)
- 2015 (1)
- 2014 (1)

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精炼

分类

排序方式: 日期 被引频次 使用次数 相关性 更多 ▾

◀ 1 / 3 ▶

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分析检索结果

 1.

The yielding behavior of SiC under high pressure and temperature conditions

作者: Yuejian Wang

AIP Advances 卷: 10 期: 6 页: 065209 (5 pp.) 出版年: June 2020

 出版商处的免费全文 查看摘要 ▾

temperature $1.37315E+03$ K
pressure $7.4E+09$ Pa

被引频次: 0

(来自 Web of Science 的核心合集)

使用次数 ▾

 2.

Highly electrically and thermally conductive silicon carbide-graphene composites with yttria and scandia additives

作者: Hanzel, O.; Lences, Z.; Young-Wook Kim; 等.

Journal of the European Ceramic Society 卷: 40 期: 2 页: 241-50 出版年: Feb. 2020

 出版商处的全文 查看摘要 ▾

temperature $2.07315E+03$ K
pressure $3.0E+06$ Pa

被引频次: 3

(来自 Web of Science 的核心合集)

使用次数 ▾

 3.

Measuring the effects of heat treatment on SiC/SiC ceramic matrix composites using Raman spectroscopy

作者: Knauf, M.W.; Przybyla, C.P.; Ritchey, A.J.; 等.

Journal of the American Ceramic Society 卷: 103 期: 2 页: 1293-303 出版年: 2020

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temperature $1.17315E+03$ to $1.57315E+03$ K
pressure $3.0E+08$ Pa

被引频次: 2

(来自 Web of Science 的核心合集)

使用次数 ▾

 4.

Influence of warm temperature (0.3-0.5Tm) uniaxial compression on the distribution of reinforcing particles in a 2124-Al/10%SiC MMC

作者: Gxowa-Penxa, Z.; Chown, L.H.; Govender, G.

会议信息: Conference of the South African Advanced Materials Initiative (CSAAMI 2019) 会议地点: Vanderbijlpark, South Africa 会议日期: 22-25 Oct. 2019

IOP Conference Series: Materials Science and Engineering 卷: 655 页: 012037 (8 pp.) 出版年: 2019

temperature $7.6315E+02$ K
pressure $9.5E+07$ Pa

被引频次: 0

(来自 Web of Science 的核心合集)

使用次数 ▾

检索结果: 5

(来自 Inspec)

您的检索: 主题: (semiconductor devices) AND 压力: >=(9.32E+06) AND 温度: >=(7.35E+02) AND 化学物质索引: (SiC/bin) AND 处理类型: (Practical)

时间跨度: 所有年份. 索引: Inspec.

...更少内容

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精炼检索结果

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过滤结果依据:

  开放获取 (1)

出版年

 2013 (1)

 2007 (1)

 排序方式: [日期](#)  被引频次 使用次数 相关性 更多 ▾

◀ 1 / 1 ▶

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 1. **The capacitance and temperature effects of the SiC- and Si-based MEMS pressure sensor**

作者: Marsi, N.; Majlis, B.Y.; Mohd-Yasin, F.; 等.

会议信息: 3rd ISESCO International Workshop and Conference on Nanotechnology 2012 (IWCN2012) 会议地点: Selangor, Malaysia 会议日期: 5-7 Dec. 2012

Journal of Physics: Conference Series 卷: 431 页: 012022 (9 pp.) 出版年: 2013

 ▾

 2. **SiC based pressure sensor for high-temperature environments**

作者: Wieczorek, G.; Schellin, B.; Obermeier, E.; 等.

会议信息: IEEE Sensors 2007 Conference 会议地点: Atlanta, GA, USA 会议日期: 28-31 Oct. 2007

IEEE Sensors 2007 Conference 页: 748-51 出版年: 2007

 ▾

 3. **Stress control of polycrystalline 3C-SiC films in a large-scale LPCVD reactor using 1,3-disilabutane and dichlorosilane as precursors**

作者: Roper, C.S.; Howe, R.T.; Maboudian, R.

Journal of Micromechanics and Microengineering 卷: 16 期: 12 页: 2736-9 出版年: Dec. 2006

 ▾

分析检索结果

被引频次: 5

(来自 Web of Science 的核心合集)

使用次数 ▾

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使用次数 ▾

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